

FDN338P

P-Channel 2.5V Specified PowerTrench[®] MOSFET -20V, -1.6A, 115mΩ

Product Overview

For complete documentation, see the data sheet.

This P-Channel 2.5V specified MOSFET uses an advanced low voltage PowerTrench process. It has been optimized for battery power management applications.

Features

- -1.6 A, -20 V
- $R_{DS(ON)} = 115\text{ m}\Omega$ @ $V_{GS} = -4.5\text{ V}$
- $R_{DS(ON)} = 155\text{ m}\Omega$ @ $V_{GS} = -2.5\text{ V}$
- Fast switching speed
- High performance trench technology for extremely low $R_{DS(ON)}$
- SuperSOT™ -3 provides low $R_{DS(ON)}$ and 30% higherpower handling capability than SOT23 in the samefootprint

Applications

- This product is general usage and suitable for many different applications.
- Battery Management
- Load Switch
- Battery Protection

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS}^{(BR)}$ Min (V)	V_{GS}^{Max} (V)	$V_{GS}^{(t)}$ Max (V)	I_D Max (A)	P_D Max (W)	$R_{DS(on)}^{Max}$ @ $V_{GS} = 2.5\text{ V}$ (mΩ)	$R_{DS(on)}^{Max}$ @ $V_{GS} = 4.5\text{ V}$ (mΩ)	$R_{DS(on)}^{Max}$ @ $V_{GS} = 10\text{ V}$ (mΩ)	Q_g Typ @ $V_{GS} = 4.5\text{ V}$ (nC)	Q_g Typ @ $V_{GS} = 10\text{ V}$ (nC)	C_{iss} Typ (pF)	Package Type
FDN338P	0.1032		Active	P-Channel	Single	-20	8	-1.5	-1.6	0.5	155	115	-	7.2	4.4	451	SOT-23-3